



# BTA310X-800E

## 3Q Hi-Com Triac

Rev. 1 — 23 April 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers.

### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

### 1.3 Applications

- Industrial and domestic heating circuits
- Motor controls e.g. washing machines and vacuum cleaners
- Refrigeration and air-conditioner compressor controls

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	800	V
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; see <a href="#">Figure 4</a> ; see <a href="#">Figure 5</a>	-	-	85	A
$T_{\text{j}}$	junction temperature		-	-	125	°C
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{h}} \leq 73\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 3</a>	-	-	10	A

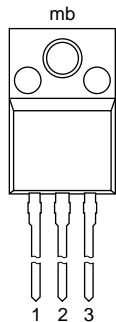
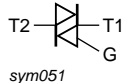


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; see <a href="#">Figure 7</a>	0.5	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; see <a href="#">Figure 7</a>	0.5	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; see <a href="#">Figure 7</a>	0.5	-	10	mA
Dynamic characteristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	50	-	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 10 A; dV <sub>com</sub> /dt = 1 V/μs; gate open circuit	6	-	-	A/ms

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

SOT186A (TO-220F)

## 3. Ordering information

Table 3. Ordering information

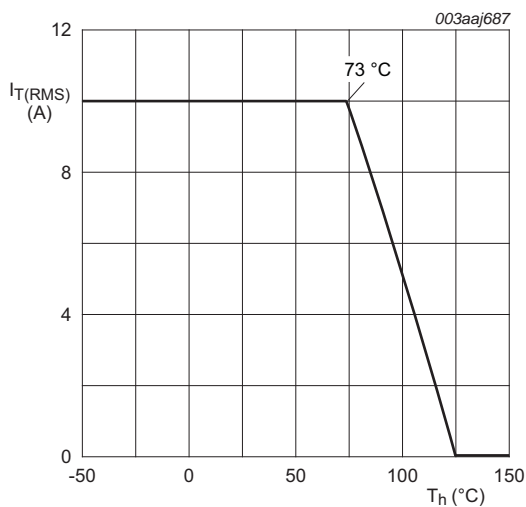
Type number	Package		
	Name	Description	Version
BTA310X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 4. Limiting values

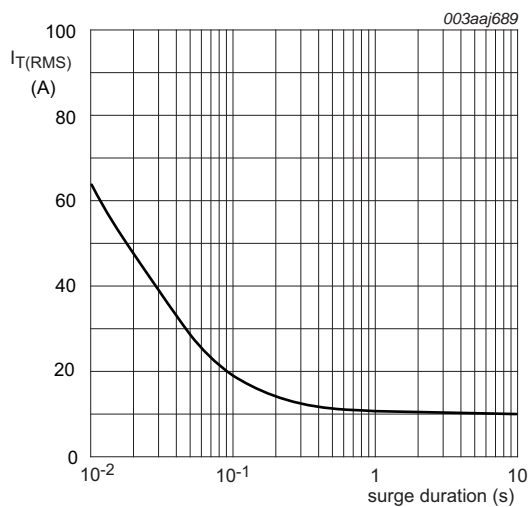
**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_h \leq 73^\circ\text{C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 3</a>	-	10	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; see <a href="#">Figure 4</a> ; see <a href="#">Figure 5</a>	-	85	A
		full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$ ; $t_p = 20\text{ ms}$	-	93	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	36.1	$\text{A}^2\text{s}$
$dl_T/dt$	rate of rise of on-state current	$I_T = 20\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dl_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current		-	2	A
$P_{\text{GM}}$	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
$T_{\text{stg}}$	storage temperature		-40	150	$^\circ\text{C}$
$T_j$	junction temperature		-	125	$^\circ\text{C}$



**Fig 1. RMS on-state current as a function of heatsink temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_h = 73^\circ\text{C}$

**Fig 2. RMS on-state current as a function of surge duration; maximum values**

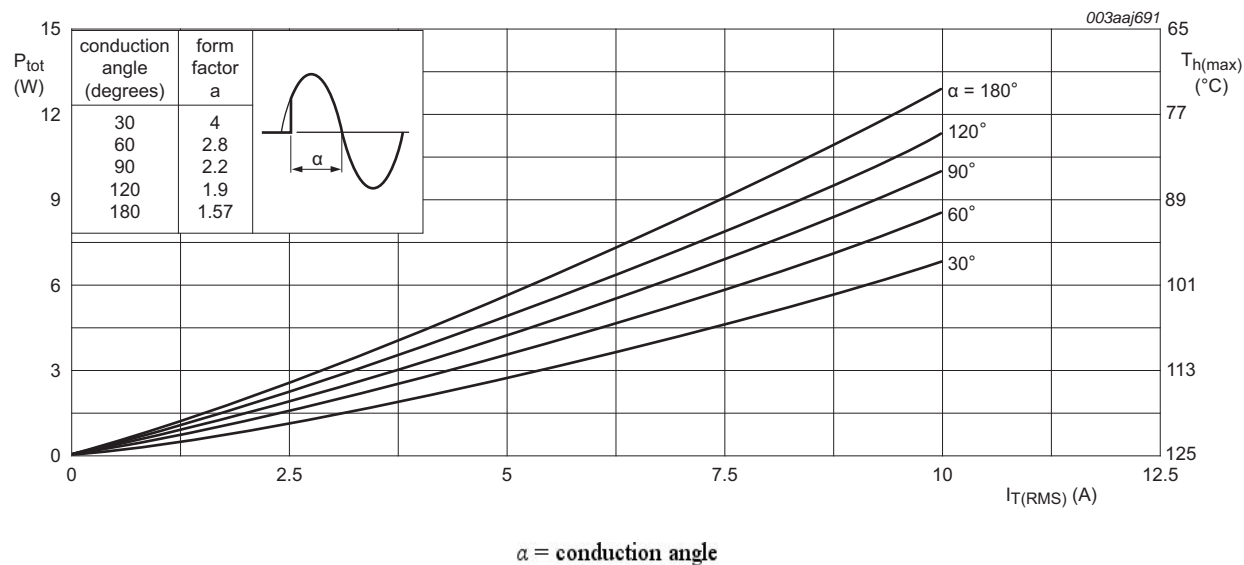


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

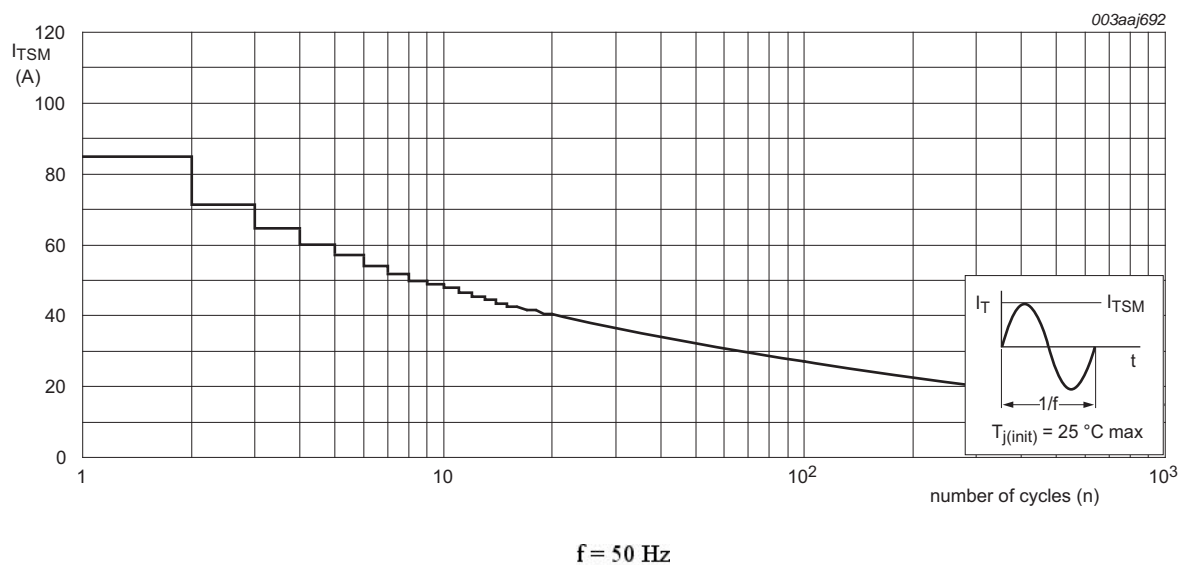
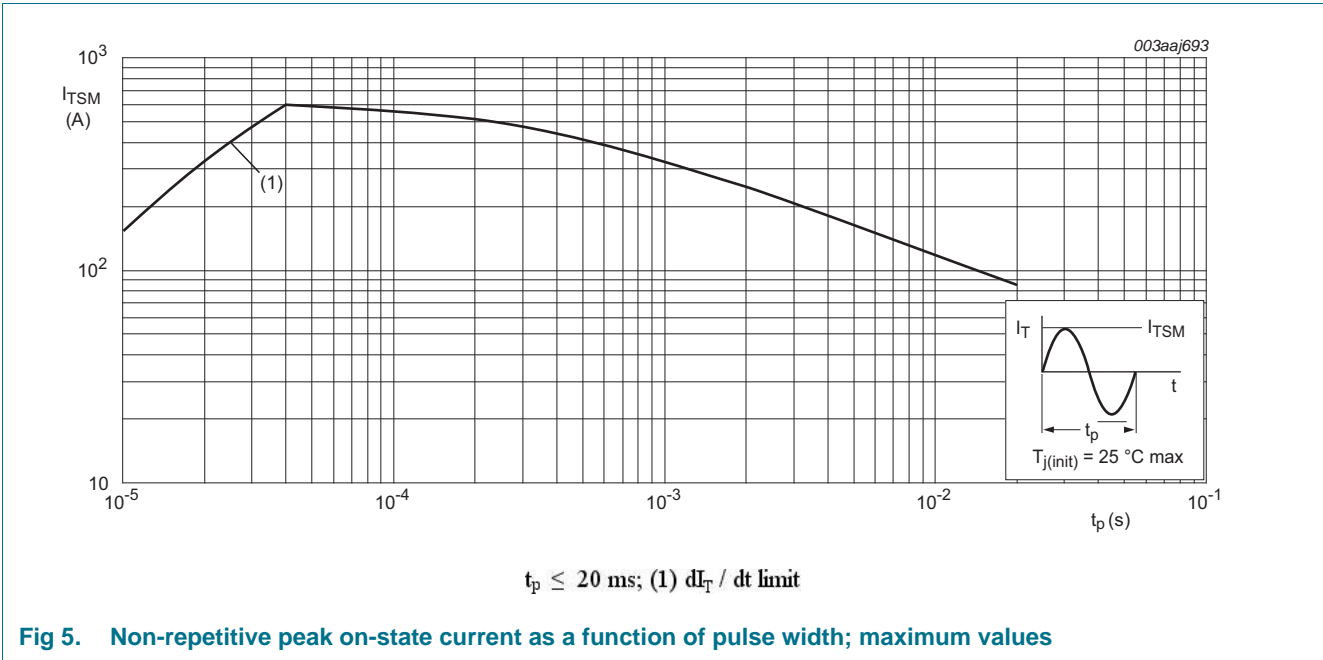


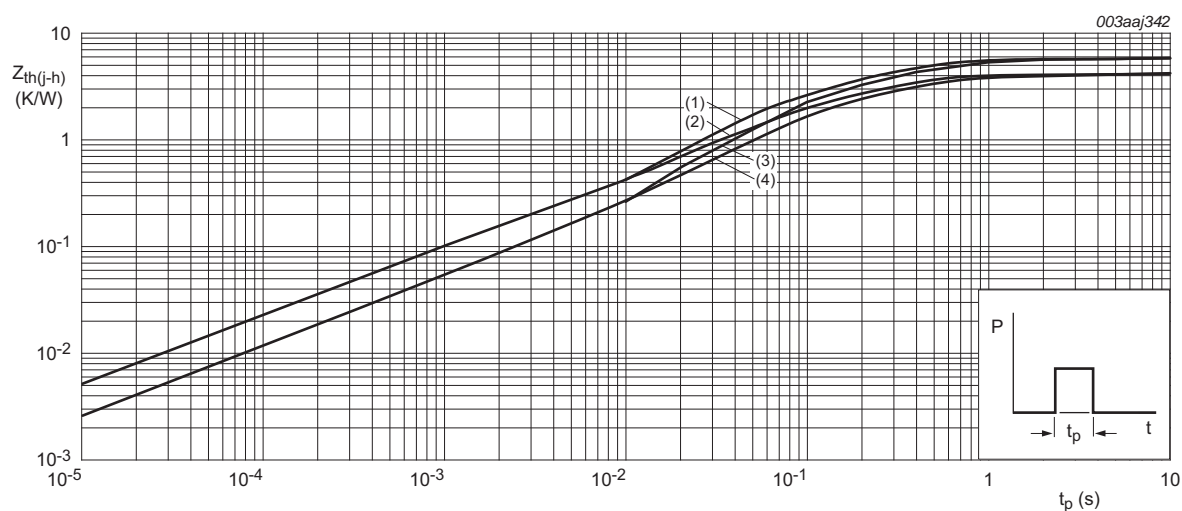
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see <a href="#">Figure 6</a>	-	-	4	K/W
		full cycle or half cycle; without heatsink compound; see <a href="#">Figure 6</a>	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



**Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration**

## 6. Isolation characteristics

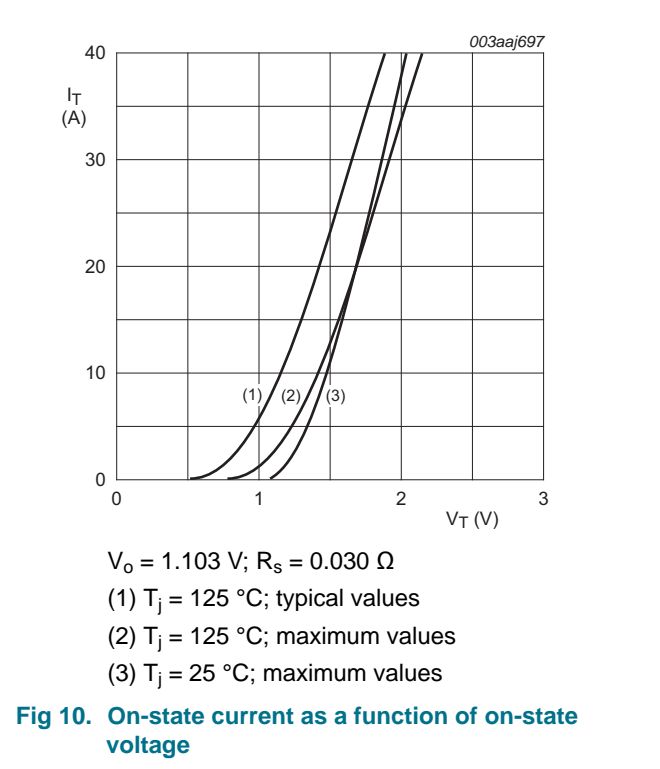
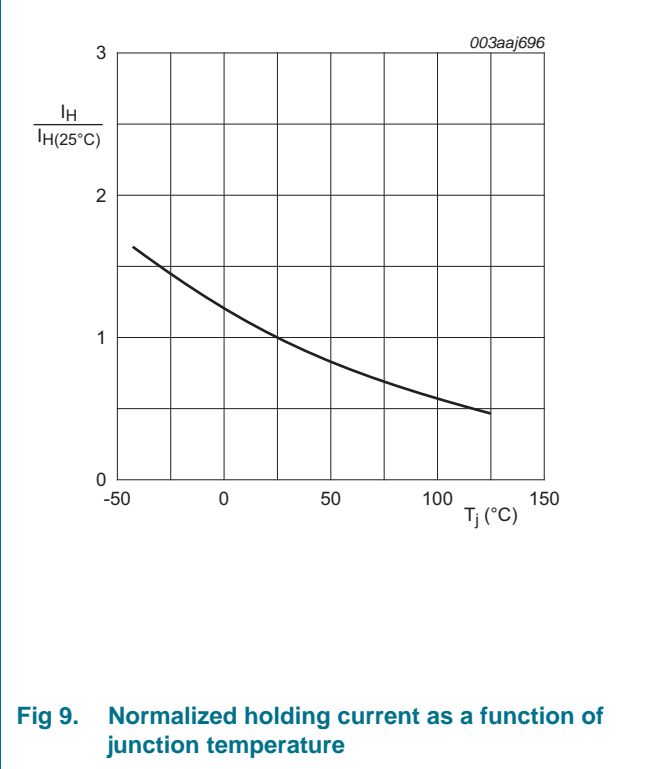
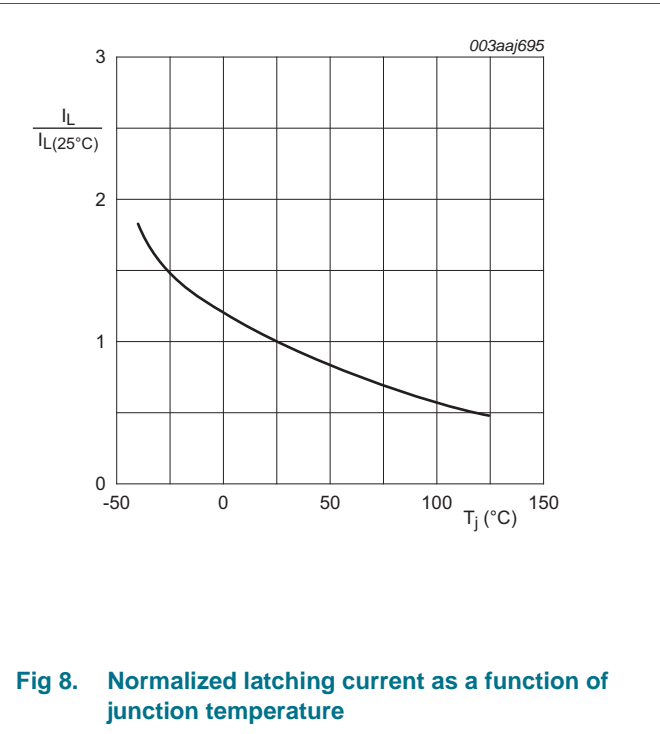
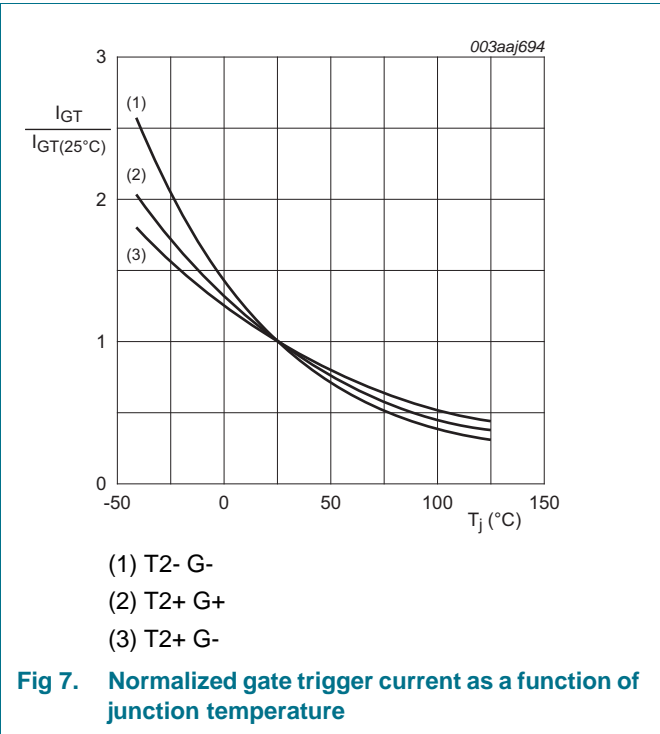
**Table 6. Isolation characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1\text{ MHz}$ ; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	0.5	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	0.5	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 7</a>	0.5	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 8</a>	-	-	25	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 8</a>	-	-	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 8</a>	-	-	25	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 9</a>	-	-	15	mA
$V_T$	on-state voltage	$I_T = 12\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 10</a>	-	1.25	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; see <a href="#">Figure 11</a>	-	0.7	1.5	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; see <a href="#">Figure 11</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	50	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	2	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	3	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 10\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	6	-	-	A/ms





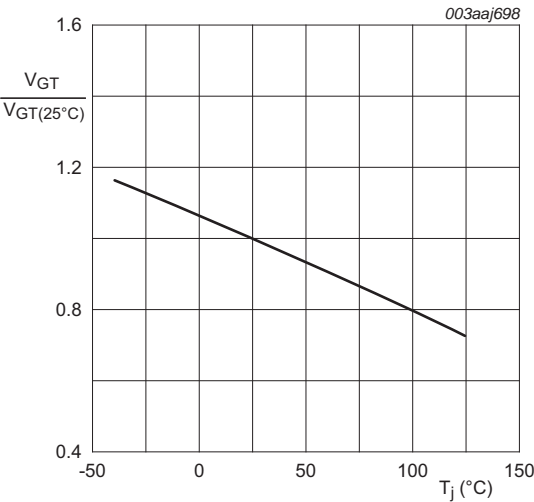


Fig 11. Normalized gate trigger voltage as a function of junction temperature

8. Package outline

Plastic single-ended package; isolated heatsink mounted;  
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

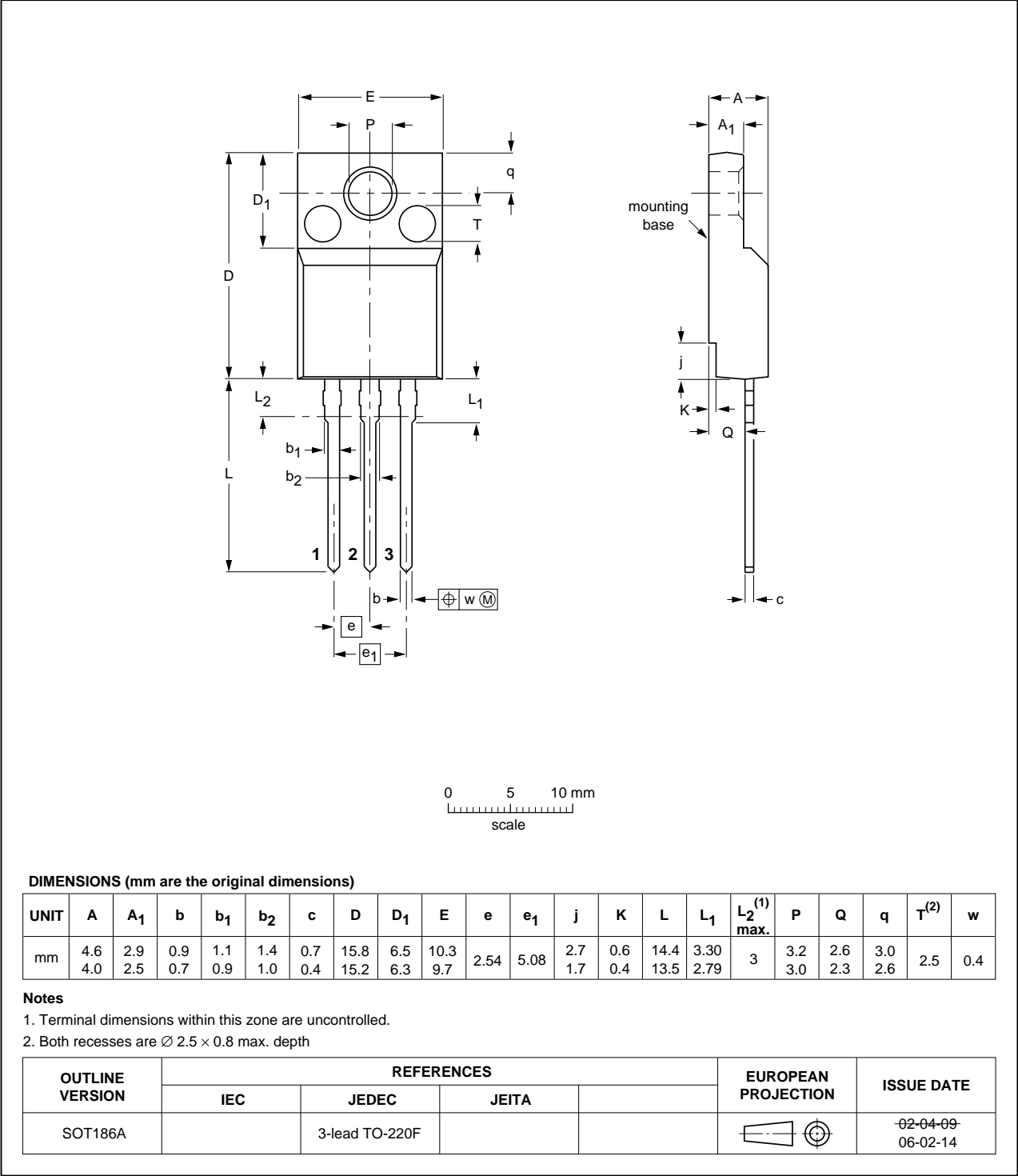


Fig 12. Package outline SOT186A (TO-220F)

## 9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA310X-800E v.1	20120423	Product data sheet	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status <sup>[1] [2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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